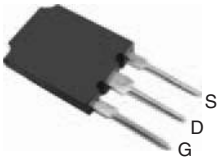
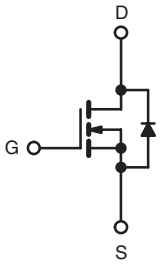
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Max.) (Ω)	V_{GS} = 10 V	0.13
Q_g (Max.) (nC)	180	
Q_{gs} (nC)	46	
Q_{gd} (nC)	71	
Configuration	Single	

SUPER-247™





N-Channel MOSFET

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} Specified
- Lead (Pb)-free Available

Available

RoHS* COMPLIANT

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

TYPICAL SMPS TOPOLOGIES

- Full Bridge Converters
- Power Factor Correction Boost

ORDERING INFORMATION	
Package	SUPER-247™
Lead (Pb)-free	IRFPS37N50APbF
	SiHFPS37N50A-E3
SnPb	IRFPS37N50A
	SiHFPS37N50A

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	500	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	36	A
		T_C = 100 °C		23	
Pulsed Drain Current[a]			I_{DM}	144	
Linear Derating Factor				3.6	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	1260	mJ
Repetitive Avalanche Current[a]			I_{AR}	36	A
Repetitive Avalanche Energy[a]			E_{AR}	44	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	446	W
Peak Diode Recovery dV/dt[c]			dV/dt	3.5	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[d]	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Starting T_J = 25 °C, L = 1.94 mH, R_G = 25 Ω, I_{AS} = 36 A (see fig. 12).
c. I_{SD} ≤ 36 A, dI/dt ≤ 145 A/µs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.28	

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		500	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 30 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V		-	-	25	µA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 150 °C		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 22 A[b]	-	-	0.13	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 22 A[b]		20	-	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	5579	-	pF
Output Capacitance	C_{oss}			-	810	-	
Reverse Transfer Capacitance	C_{rss}			-	36	-	
Output Capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 1.0 V , f = 1.0 MHz	-	7905	-	
			V_{DS} = 400 V , f = 1.0 MHz	-	221	-	
Effective Output Capacitance	C_{oss} eff.		V_{DS} = 0 V to 400 V	-	400	-	
Total Gate Charge	Q_g	V_{GS} = 10 V	I_D = 36 A, V_{DS} = 400 V, see fig. 6 and 13[b]	-	-	180	nC
Gate-Source Charge	Q_{gs}			-	-	46	
Gate-Drain Charge	Q_{gd}			-	-	71	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 250 V, I_D = 36 A, R_G = 2.15 Ω, R_D = 7.0 Ω, see fig. 10[b]		-	23	-	ns
Rise Time	t_r			-	98	-	
Turn-Off Delay Time	$t_{d(off)}$			-	52	-	
Fall Time	t_f			-	80	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	36	A
Pulsed Diode Forward Current[a]	I_{SM}			-	-	144	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 36 A, V_{GS} = 0 V[b]		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 36 A, dI/dt = 100 A/µs[b]		-	570	860	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	8.6	13	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.

c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS}.